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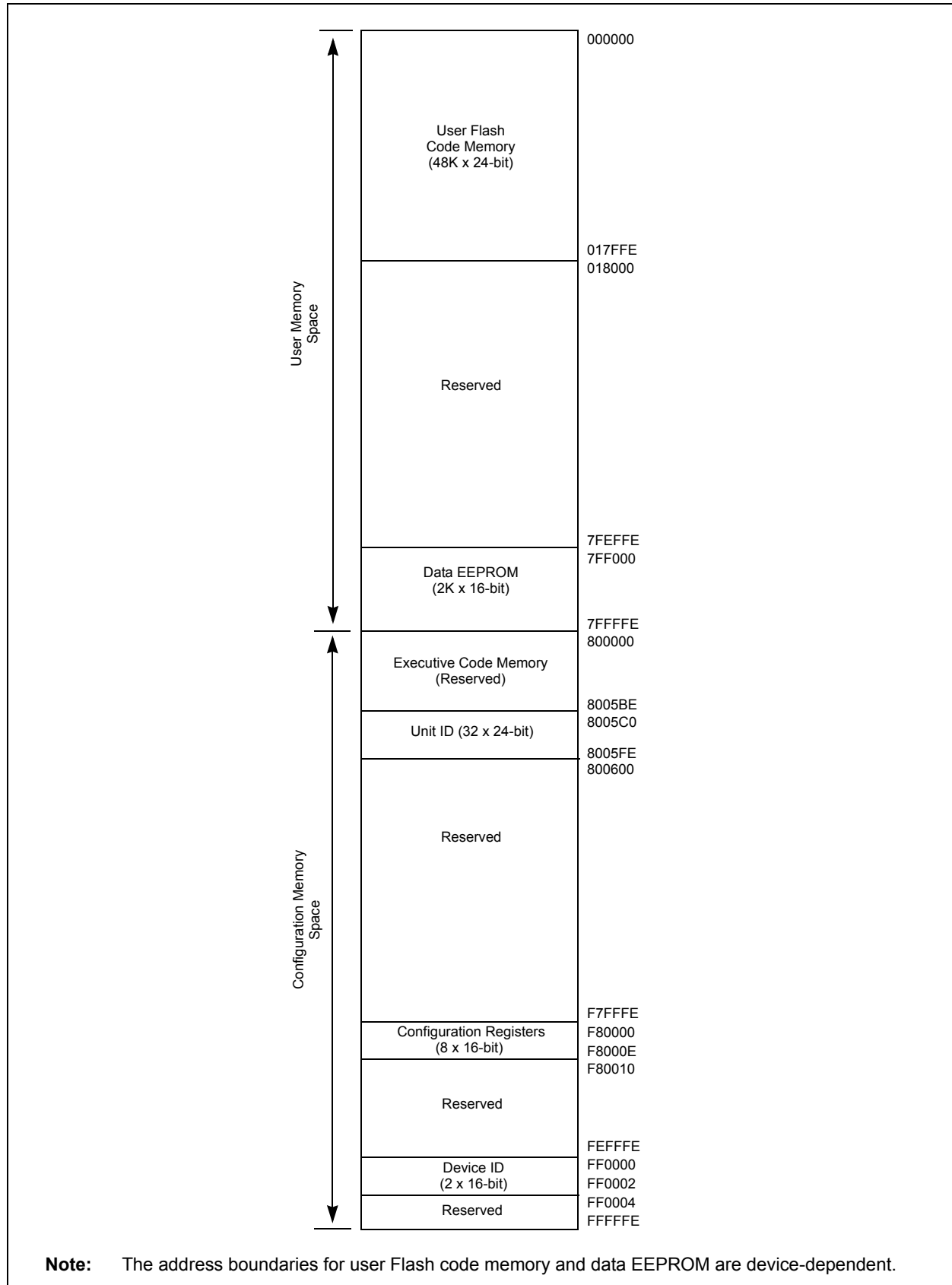
Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	I ² C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	20
Program Memory Size	12KB (4K x 24)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	28-VQFN Exposed Pad
Supplier Device Package	28-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f2012t-20e-ml

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FIGURE 2-2: PROGRAM MEMORY MAP

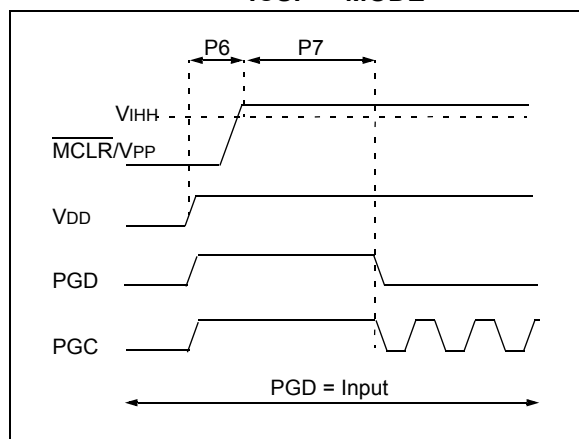


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5.2 Entering Enhanced ICSP Mode

The Enhanced ICSP mode is entered by holding PGC and PGD high, and then raising MCLR/VPP to VIH (high voltage), as illustrated in Figure 5-2. In this mode, the code memory, data EEPROM and Configuration bits can be efficiently programmed using the programming executive commands that are serially transferred using PGC and PGD.

FIGURE 5-2: ENTERING ENHANCED ICSP™ MODE



Note 1: The sequence that places the device into Enhanced ICSP mode places all unused I/Os in the high-impedance state.

2: Before entering Enhanced ICSP mode, clock switching must be disabled using ICSP, by programming the FCKSM<1:0> bits in the FOSC Configuration register to '11' or '10'.

3: When in Enhanced ICSP mode, the SPI output pin (SDO1) will toggle while the device is being programmed.

5.3 Chip Erase

Before a chip can be programmed, it must be erased. The Bulk Erase command (**ERASEB**) is used to perform this task. Executing this command with the MS command field set to 0x3 erases all code memory, data EEPROM and code-protect Configuration bits. The Chip Erase process sets all bits in these three memory regions to '1'.

Since non-code-protect Configuration bits cannot be erased, they must be manually set to '1' using multiple **PROGC** commands. One **PROGC** command must be sent for each Configuration register (see [Section 5.7 "Configuration Bits Programming"](#)).

If Advanced Security features are enabled, then individual Segment Erase operations would need to be performed, depending on which segment needs to be programmed at a given stage of system programming. The user should have the flexibility to select specific segments for programming.

Note: The Device ID registers cannot be erased. These registers remain intact after a Chip Erase is performed.

5.4 Blank Check

The term "Blank Check" means to verify that the device has been successfully erased and has no programmed memory cells. A blank or erased memory cell reads as '1'. The following memories must be blank checked:

- All implemented code memory
- All implemented data EEPROM
- All Configuration bits (for their default value)

The Device ID registers (0xFF0000:0xFF0002) can be ignored by the Blank Check since this region stores device information that cannot be erased. Additionally, all unimplemented memory space should be ignored from the Blank Check.

The **QBLANK** command is used for the Blank Check. It determines if the code memory and data EEPROM are erased by testing these memory regions. A 'BLANK' or 'NOT BLANK' response is returned. The **READD** command is used to read the Configuration registers. If it is determined that the device is not blank, it must be erased (see [Section 5.3 "Chip Erase"](#)) before attempting to program the chip.

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TABLE 5-5: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F4011/4012 AND dsPIC30F5011/5013

Bit Field	Register	Description
FCKSM<1:0>	FOSC	Clock Switching Mode 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<1:0>	FOSC	Oscillator Source Selection on POR 11 = Primary Oscillator 10 = Internal Low-Power RC Oscillator 01 = Internal Fast RC Oscillator 00 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<3:0>	FOSC	Primary Oscillator Mode 1111 = ECIO w/PLL 16X – External Clock mode with 16X PLL. OSC2 pin is I/O 1110 = ECIO w/PLL 8X – External Clock mode with 8X PLL. OSC2 pin is I/O 1101 = ECIO w/PLL 4X – External Clock mode with 4X PLL. OSC2 pin is I/O 1100 = ECIO – External Clock mode. OSC2 pin is I/O 1011 = EC – External Clock mode. OSC2 pin is system clock output (Fosc/4) 1010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 1001 = ERC – External RC Oscillator mode. OSC2 pin is system clock output (Fosc/4) 1000 = ERCIO – External RC Oscillator mode. OSC2 pin is I/O 0111 = XT w/PLL 16X – XT Crystal Oscillator mode with 16X PLL 0110 = XT w/PLL 8X – XT Crystal Oscillator mode with 8X PLL 0101 = XT w/PLL 4X – XT Crystal Oscillator mode with 4X PLL 0100 = XT – XT Crystal Oscillator mode (4 MHz-10 MHz crystal) 0011 = FRC w/PLL 16x – Internal fast RC oscillator with 16x PLL. OSC2 pin is I/O 0010 = HS – HS Crystal Oscillator mode (10 MHz-25 MHz crystal) 0001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0000 = XTL – XTL Crystal Oscillator mode (200 kHz-4 MHz crystal)

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TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015

Bit Field	Register	Description
FCKSM<1:0>	FOSC	Clock Switching Mode 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<2:0>	FOSC	Oscillator Source Selection on POR 111 = Primary Oscillator 110 = Reserved 101 = Reserved 100 = Reserved 011 = Reserved 010 = Internal Low-Power RC Oscillator 001 = Internal Fast RC Oscillator (no PLL) 000 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<4:0>	FOSC	Primary Oscillator Mode (when FOS<2:0> = 111b) 11xxx = Reserved (do not use) 10111 = HS/3 w/PLL 16X – HS/3 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10110 = HS/3 w/PLL 8X – HS/3 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10101 = HS/3 w/PLL 4X – HS/3 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10100 = Reserved (do not use) 10011 = HS/2 w/PLL 16X – HS/2 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10010 = HS/2 w/PLL 8X – HS/2 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10001 = HS/2 w/PLL 4X – HS/2 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10000 = Reserved (do not use) 01111 = ECIO w/PLL 16x – External clock with 16x PLL. OSC2 pin is I/O 01110 = ECIO w/PLL 8x – External clock with 8x PLL. OSC2 pin is I/O 01101 = ECIO w/PLL 4x – External clock with 4x PLL. OSC2 pin is I/O 01100 = Reserved (do not use) 01011 = Reserved (do not use) 01010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 01001 = Reserved (do not use) 01000 = Reserved (do not use) 00111 = XT w/PLL 16X – XT crystal oscillator with 16X PLL 00110 = XT w/PLL 8X – XT crystal oscillator with 8X PLL 00101 = XT w/PLL 4X – XT crystal oscillator with 4X PLL 00100 = Reserved (do not use) 00011 = FRC w/PLL 16x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 00010 = Reserved (do not use) 00001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 00000 = Reserved (do not use)

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TABLE 5-7: CONFIGURATION BITS DESCRIPTION

Bit Field	Register	Description
FWPSA<1:0>	FWDT	Watchdog Timer Prescaler A 11 = 1:512 10 = 1:64 01 = 1:8 00 = 1:1
FWPSB<3:0>	FWDT	Watchdog Timer Prescaler B 1111 = 1:16 1110 = 1:15 . . . 0001 = 1:2 0000 = 1:1
FWDTEN	FWDT	Watchdog Enable 1 = Watchdog enabled (LPRC oscillator cannot be disabled. Clearing the SWDTEN bit in the RCON register will have no effect) 0 = Watchdog disabled (LPRC oscillator can be disabled by clearing the SWDTEN bit in the RCON register)
MCLREN	FBORPOR	Master Clear Enable 1 = Master Clear pin (MCLR) is enabled 0 = MCLR pin is disabled
PWMPIN	FBORPOR	Motor Control PWM Module Pin Mode 1 = PWM module pins controlled by PORT register at device Reset (tri-stated) 0 = PWM module pins controlled by PWM module at device Reset (configured as output pins)
HPOL	FBORPOR	Motor Control PWM Module High-Side Polarity 1 = PWM module high-side output pins have active-high output polarity 0 = PWM module high-side output pins have active-low output polarity
LPOL	FBORPOR	Motor Control PWM Module Low-Side Polarity 1 = PWM module low-side output pins have active-high output polarity 0 = PWM module low-side output pins have active-low output polarity
BOREN	FBORPOR	PBOR Enable 1 = PBOR enabled 0 = PBOR disabled
BORV<1:0>	FBORPOR	Brown-out Voltage Select 11 = 2.0V (not a valid operating selection) 10 = 2.7V 01 = 4.2V 00 = 4.5V
FPWRT<1:0>	FBORPOR	Power-on Reset Timer Value Select 11 = PWRT = 64 ms 10 = PWRT = 16 ms 01 = PWRT = 4 ms 00 = Power-up Timer disabled
RBS<1:0>	FBS	Boot Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = No Data RAM is reserved for Boot Segment 10 = Small-sized Boot RAM [128 bytes of RAM are reserved for Boot Segment] 01 = Medium-sized Boot RAM [256 bytes of RAM are reserved for Boot Segment] 00 = Large-sized Boot RAM [512 bytes of RAM are reserved for Boot Segment in dsPIC30F5011/5013, and 1024 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015]

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TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

Bit Field	Register	Description
EBS	FBS	Boot Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = No Data EEPROM is reserved for Boot Segment 0 = 128 bytes of Data EEPROM are reserved for Boot Segment in dsPIC30F5011/5013, and 256 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015
BSS<2:0>	FBS	Boot Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 111 = No Boot Segment 110 = Standard security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 101 = Standard security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x000FFF] 100 = Standard security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FFF] 011 = No Boot Segment 010 = High security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 001 = High security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x000FFF] 000 = High security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FFF]
BWRP	FBS	Boot Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = Boot Segment program memory is not write-protected 0 = Boot Segment program memory is write-protected
RSS<1:0>	FSS	Secure Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = No Data RAM is reserved for Secure Segment 10 = Small-sized Secure RAM [(256 – N) bytes of RAM are reserved for Secure Segment] 01 = Medium-sized Secure RAM [(768 – N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/5013, and (2048 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 00 = Large-sized Secure RAM [(1024 – N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/5013, and (4096 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] where N = Number of bytes of RAM reserved for Boot Sector.
ESS<1:0>	FSS	Secure Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = No Data EEPROM is reserved for Secure Segment 10 = Small-sized Secure Data EEPROM [(128 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (256 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 01 = Medium-sized Secure Data EEPROM [(256 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (512 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 00 = Large-sized Secure Data EEPROM [(512 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, (1024 – N) bytes in dsPIC30F6011A/6013A, and (2048 – N) bytes in dsPIC30F6010A/6012A/6014A/6015] where N = Number of bytes of Data EEPROM reserved for Boot Sector.

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TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

Bit Field	Register	Description
SSS<2:0>	FSS	Secure Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 111 = No Secure Segment 110 = Standard security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 101 = Standard security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 100 = Standard security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF] 011 = No Secure Segment 010 = High security; Small-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x001FFF] 001 = High security; Medium-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x003FFF] 000 = High security; Large-sized Secure Program Flash [Secure Segment starts after BS and ends at 0x007FFF]
SWRP	FSS	Secure Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = Secure Segment program memory is not write-protected 0 = Secure program memory is write-protected
GSS<1:0>	FGS	General Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 11 = Code protection is disabled 10 = Standard security code protection is enabled 0x = High security code protection is enabled
GCP	FGS	General Segment Program Memory Code Protection (present in all devices except dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015) 1 = General Segment program memory is not code-protected 0 = General Segment program memory is code-protected
GWRP	FGS	General Segment Program Memory Write Protection 1 = General Segment program memory is not write-protected 0 = General Segment program memory is write-protected
BKBUG	FICD	Debugger/Emulator Enable 1 = Device will reset into Operational mode 0 = Device will reset into Debug/Emulation mode
COE	FICD	Debugger/Emulator Enable 1 = Device will reset into Operational mode 0 = Device will reset into Clip-on Emulation mode
ICS<1:0>	FICD	ICD Communication Channel Select 11 = Communicate on PGC/EMUC and PGD/EMUD 10 = Communicate on EMUC1 and EMUD1 01 = Communicate on EMUC2 and EMUD2 00 = Communicate on EMUC3 and EMUD3
RESERVED	FBS, FSS, FGS	Reserved (read as '1', write as '1')
—	All	Unimplemented (read as '0', write as '0')

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6.0 OTHER PROGRAMMING FEATURES

6.1 Erasing Memory

Memory is erased by using an `ERASEB`, `ERASED` or `ERASEP` command, as detailed in [Section 8.5 “Command Descriptions”](#). Code memory can be erased by row using `ERASEP`. Data EEPROM can be erased by row using `ERASED`. When memory is erased, the affected memory locations are set to ‘1’s.

`ERASEB` provides several Bulk Erase options. Performing a Chip Erase with the `ERASEB` command clears all code memory, data EEPROM and code protection registers. Alternatively, `ERASEB` can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in [Table 6-1](#).

TABLE 6-1: ERASE OPTIONS

Command	Affected Region
<code>ERASEB</code>	Entire chip ⁽¹⁾ or all code memory or all data EEPROM, or erase by segment
<code>ERASED</code>	Specified rows of data EEPROM
<code>ERASEP</code> ⁽²⁾	Specified rows of code memory

- Note 1:** The system operation Configuration registers and device ID registers are not erasable.
- 2:** `ERASEP` cannot be used to erase code-protect Configuration bits. These bits must be erased using `ERASEB`.

6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using `ERASEP` and `ERASED`, respectively. You can then reprogram the modified rows with the `PROGP` and `PROGD` command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the `PROGP` command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the `ERASEB` command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select)

field in the `ERASEB` command. The code-protect Configuration bits can then be reprogrammed using the `PROGC` command.

Note: If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

6.3 Reading Memory

The `READD` command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. `READD` can be used to return the entire contents of data EEPROM.

The `READP` command reads the code memory of the device. This command only returns 24-bit data packed as described in [Section 8.3 “Packed Data Format”](#). `READP` can be used to read up to 32K instruction words of code memory.

Note: Reading an unimplemented memory location causes the programming executive to reset. All `READD` and `READP` commands **must** specify only valid memory locations.

6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The `QVER` command performs this function. See [Section 8.5.11 “QVER Command”](#) for more details about this command.

6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

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6.6 Configuration Information in the Hexadecimal File

To allow portability of code, the programmer must read the Configuration register locations from the hexadecimal file. If configuration information is not present in the hexadecimal file, a simple warning message should be issued by the programmer. Similarly, while saving a hexadecimal file, all configuration information must be included. An option to not include the configuration information can be provided.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

6.7 Unit ID

The dsPIC30F devices contain 32 instructions of Unit ID. These are located at addresses 0x8005C0 through 0x8005FF. The Unit ID can be used for storing product information such as serial numbers, system manufacturing dates, manufacturing lot numbers and other such application-specific information.

A Bulk Erase does not erase the Unit ID locations. Instead, erase all executive memory using steps 1-4 as shown in [Table 12-1](#), and program the Unit ID along with the programming executive. Alternately, use a Row Erase to erase the row containing the Unit ID locations.

6.8 Checksum Computation

Checksums for the dsPIC30F are 16 bits in size. The checksum is to total sum of the following:

- Contents of code memory locations
- Contents of Configuration registers

[Table A-1](#) describes how to calculate the checksum for each device. All memory locations are summed one byte at a time, using only their native data size. More specifically, Configuration and device ID registers are summed by adding the lower two bytes of these locations (the upper byte is ignored), while code memory is summed by adding all three bytes of code memory.

Note: The checksum calculation differs depending on the code-protect setting. [Table A-1](#) describes how to compute the checksum for an unprotected device and a read-protected device. Regardless of the code-protect setting, the Configuration registers can always be read.

7.0 PROGRAMMER – PROGRAMMING EXECUTIVE COMMUNICATION

7.1 Communication Overview

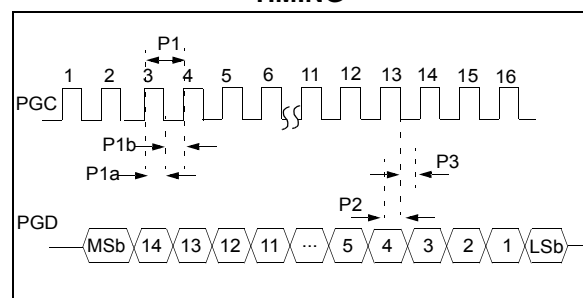
The programmer and programming executive have a master-slave relationship, where the programmer is the master programming device and the programming executive is the slave.

All communication is initiated by the programmer in the form of a command. Only one command at a time can be sent to the programming executive. In turn, the programming executive only sends one response to the programmer after receiving and processing a command. The programming executive command set is described in [Section 8.0 “Programming Executive Commands”](#). The response set is described in [Section 9.0 “Programming Executive Responses”](#).

7.2 Communication Interface and Protocol

The Enhanced ICSP interface is a 2-wire SPI interface implemented using the PGC and PGD pins. The PGC pin is used as a clock input pin, and the clock source must be provided by the programmer. The PGD pin is used for sending command data to, and receiving response data from, the programming executive. All serial data is transmitted on the falling edge of PGC and latched on the rising edge of PGD. All data transmissions are sent Most Significant bit (MSb) first, using 16-bit mode (see [Figure 7-1](#)).

FIGURE 7-1: PROGRAMMING EXECUTIVE SERIAL TIMING



Since a 2-wire SPI interface is used, and data transmissions are bidirectional, a simple protocol is used to control the direction of PGD. When the programmer completes a command transmission, it releases the PGD line and allows the programming executive to drive this line high. The programming executive keeps the PGD line high to indicate that it is processing the command.

After the programming executive has processed the command, it brings PGD low for 15 μ sec to indicate to the programmer that the response is available to be

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8.0 PROGRAMMING EXECUTIVE COMMANDS

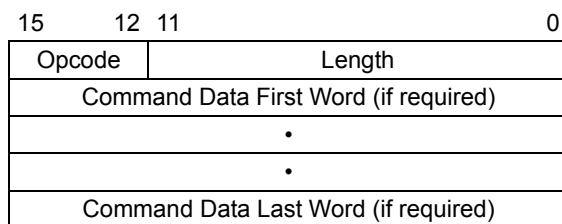
8.1 Command Set

The programming executive command set is shown in [Table 8-1](#). This table contains the opcode, mnemonic, length, time out and description for each command. Functional details on each command are provided in the command descriptions (see [Section 8.5 “Command Descriptions”](#)).

8.2 Command Format

All programming executive commands have a general format consisting of a 16-bit header and any required data for the command (see [Figure 8-1](#)). The 16-bit header consists of a 4-bit opcode field, which is used to identify the command, followed by a 12-bit command length field.

FIGURE 8-1: COMMAND FORMAT



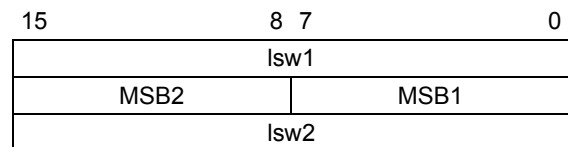
The command opcode must match one of those in the command set. Any command that is received which does not match the list in [Table 8-1](#) will return a “NACK” response (see [Section 9.2.1 “Opcode Field”](#)).

The command length is represented in 16-bit words since the SPI operates in 16-bit mode. The programming executive uses the Command Length field to determine the number of words to read from the SPI port. If the value of this field is incorrect, the command will not be properly received by the programming executive.

8.3 Packed Data Format

When 24-bit instruction words are transferred across the 16-bit SPI interface, they are packed to conserve space using the format shown in [Figure 8-2](#). This format minimizes traffic over the SPI and provides the programming executive with data that is properly aligned for performing table write operations.

FIGURE 8-2: PACKED INSTRUCTION WORD FORMAT



lswx: Least significant 16 bits of instruction word

MSBx: Most Significant Byte of instruction word

Note: When the number of instruction words transferred is odd, MSB2 is zero and lsw2 cannot be transmitted.

8.4 Programming Executive Error Handling

The programming executive will “NACK” all unsupported commands. Additionally, due to the memory constraints of the programming executive, no checking is performed on the data contained in the Programmer command. It is the responsibility of the programmer to command the programming executive with valid command arguments, or the programming operation may fail. Additional information on error handling is provided in [Section 9.2.3 “QE_Code Field”](#).

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11.0 ICSP™ MODE

11.1 ICSP Mode

ICSP mode is a special programming protocol that allows you to read and write to the dsPIC30F programming executive. The ICSP mode is the second (and slower) method used to program the device. This mode also has the ability to read the contents of executive memory to determine whether the programming executive is present. This capability is accomplished by applying control codes and instructions serially to the device using pins PGC and PGD.

In ICSP mode, the system clock is taken from the PGC pin, regardless of the device's oscillator Configuration bits. All instructions are first shifted serially into an internal buffer, then loaded into the Instruction register and executed. No program fetching occurs from internal memory. Instructions are fed in 24 bits at a time. PGD is used to shift data in and PGC is used as both the serial shift clock and the CPU execution clock.

Data is transmitted on the rising edge and latched on the falling edge of PGC. For all data transmissions, the Least Significant bit (LSb) is transmitted first.

Note 1: During ICSP operation, the operating frequency of PGC must not exceed 5 MHz.

2: Because ICSP is slower, it is recommended that only Enhanced ICSP (E-ICSP) mode be used for device programming, as described in [Section 5.1 "Overview of the Programming Process"](#).

11.2 ICSP Operation

Upon entry into ICSP mode, the CPU is idle. Execution of the CPU is governed by an internal state machine. A 4-bit control code is clocked in using PGC and PGD, and this control code is used to command the CPU (see [Table 11-1](#)).

The SIX control code is used to send instructions to the CPU for execution, while the REGOUT control code is used to read data out of the device via the VISI register. The operation details of ICSP mode are provided in [Section 11.2.1 "SIX Serial Instruction Execution"](#) and [Section 11.2.2 "REGOUT Serial Instruction Execution"](#).

TABLE 11-1: CPU CONTROL CODES IN ICSP™ MODE

4-bit Control Code	Mnemonic	Description
0000b	SIX	Shift in 24-bit instruction and execute.
0001b	REGOUT	Shift out the VISI register.
0010b-1111b	N/A	Reserved.

11.2.1 SIX SERIAL INSTRUCTION EXECUTION

The SIX control code allows execution of dsPIC30F assembly instructions. When the SIX code is received, the CPU is suspended for 24 clock cycles as the instruction is then clocked into the internal buffer. Once the instruction is shifted in, the state machine allows it to be executed over the next four clock cycles. While the received instruction is executed, the state machine simultaneously shifts in the next 4-bit command (see [Figure 11-2](#)).

Note 1: Coming out of the ICSP entry sequence, the first 4-bit control code is always forced to SIX and a forced NOP instruction is executed by the CPU. Five additional PGC clocks are needed on start-up, thereby resulting in a 9-bit SIX command instead of the normal 4-bit SIX command. After the forced SIX is clocked in, ICSP operation resumes as normal (the next 24 clock cycles load the first instruction word to the CPU). See [Figure 11-1](#) for details.

2: TBLRDH, TBLRDL, TBLWTH and TBLWTL instructions must be followed by a NOP instruction.

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**TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY
(EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
Step 6: Update the row address stored in NVMADRU:NVMADR. When W6 rolls over to 0x0, NVMADRU must be incremented.		
0000	430307	ADD W6, W7, W6
0000	AF0042	BTSC SR, #C
0000	EC2764	INC NVMADRU
0000	883B16	MOV W6, NVMADR
Step 7: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 8: Repeat Steps 3-7 until all rows of code memory are erased.		
Step 9: Initialize NVMADR and NVMADRU to erase executive memory and initialize W7 for row address updates.		
0000	EB0300	CLR W6
0000	883B16	MOV W6, NVMADR
0000	200807	MOV #0x80, W7
0000	883B27	MOV W7, NVMADRU
0000	200407	MOV #0x40, W7
Step 10: Set NVMCON to erase 1 row of executive memory.		
0000	24071A	MOV #0x4071, W10
0000	883B0A	MOV W10, NVMCON
Step 11: Unlock the NVMCON to erase 1 row of executive memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 12: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see Section 13.0 “AC/DC Characteristics and Timing Requirements”)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 13: Update the row address stored in NVMADR.		
0000	430307	ADD W6, W7, W6
0000	883B16	MOV W6, NVMADR
Step 14: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 15: Repeat Steps 10-14 until all 24 rows of executive memory are erased.		
Step 16: Initialize NVMADR and NVMADRU to erase data memory and initialize W7 for row address updates.		
0000	2XXXX6	MOV #<lower 16-bits of starting Data EEPROM address>, W6
0000	883B16	MOV W6, NVMADR
0000	2007F6	MOV #0x7F, W6
0000	883B16	MOV W6, NVMADRU
0000	200207	MOV #0x20, W7
Step 17: Set NVMCON to erase 1 row of data memory.		
0000	24075A	MOV #0x4075, W10
0000	883B0A	MOV W10, NVMCON

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**TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY
(EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
Step 18: Unlock the NVMCON to erase 1 row of data memory.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 19: Initiate the erase cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P13a' ms (see Section 13.0 “AC/DC Characteristics and Timing Requirements”)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 20: Update the row address stored in NVMADR.		
0000	430307	ADD W6, W7, W6
0000	883B16	MOV W6, NVMADR
Step 21: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 22: Repeat Steps 17-21 until all rows of data memory are erased.		

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11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed

during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Set the NVMCON to write 16 data words.		
0000	24005A	MOV #0x4005, W10
0000	883B0A	MOV W10, NVMCON
Step 3: Initialize the write pointer (W7) for TBLWT instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
Step 4: Load W0:W3 with the next 4 data words to program.		
0000	2xxxx0	MOV #<WORD0>, W0
0000	2xxxx1	MOV #<WORD1>, W1
0000	2xxxx2	MOV #<WORD2>, W2
0000	2xxxx3	MOV #<WORD3>, W3
Step 5: Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.		

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TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 7: Unlock the NVMCON for writing.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 8: Initiate the write cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see Section 13.0 “AC/DC Characteristics and Timing Requirements”)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 9: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 10: Repeat steps 2-9 until all data memory is programmed.		

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TABLE 12-1: PROGRAMMING THE PROGRAMMING EXECUTIVE (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 8: Set the read pointer (W6) and load the (next four write) latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BEBBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BEBBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 9: Repeat Steps 7-8 eight times to load the write latches for the 32 instructions.		
Step 10: Unlock the NVMCON for programming.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 11: Initiate the programming cycle.		
0000	A8E761	BSET NVMCON, #15
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see Section 13.0 “AC/DC Characteristics and Timing Requirements”)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #15
0000	000000	NOP
0000	000000	NOP
Step 12: Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 13: Repeat Steps 7-12 until all 23 rows of executive memory are programmed.		

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TABLE 13-1: AC/DC CHARACTERISTICS (CONTINUED)

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	Sym	Characteristic	Min	Max	Units	Conditions
P9b	TDLY5	Delay between PGD ↓ by programming executive to PGD released by programming executive	15	—	μs	—
P10	TDLY6	Delay between PGD released by programming executive to first PGC ↑ of response	5	—	μs	—
P11	TDLY7	Delay between clocking out response words	10	—	μs	—
P12a	TPROG	Row Programming cycle time	1	4	ms	ICSP mode
P12b	TPROG	Row Programming cycle time	0.8	2.6	ms	Enhanced ICSP mode
P13a	TERA	Bulk/Row Erase cycle time	1	4	ms	ICSP mode
P13b	TERA	Bulk/Row Erase cycle time	0.8	2.6	ms	Enhanced ICSP mode

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TABLE A-1: CHECKSUM COMPUTATION (CONTINUED)

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F5016	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6015	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404

Item Description:

SUM(a:b) = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

CFGB = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

APPENDIX C: REVISION HISTORY

Note: Revision histories were not recorded for revisions A through H. The previous revision (J), was published in August 2007.

Revision K (November 2010)

This version of the document includes the following updates:

- Added Note three to [Section 5.2 “Entering Enhanced ICSP Mode”](#)
- Updated the first paragraph of [Section 10.0 “Device ID”](#)
- Updated [Table 10-1: Device IDs](#)
- Removed the VARIANT bit and updated the bit definition for the DEVID register in [Table 10-2: dsPIC30F Device ID Registers](#)
- Removed the VARIANT bit and updated the bit field definition and description for the DEVID register in [Table 10-3: Device ID Bits Description](#)
- Updated Note 3 in [Section 11.3 “Entering ICSP Mode”](#)
- Updated Step 11 in [Table 11-4: Serial Instruction Execution for Bulk Erasing Program Memory \(Only in Normal-voltage Systems\)](#)
- Updated Steps 5, 12 and 19 in [Table 11-5: Serial Instruction Execution for Erasing Program Memory \(Either in Low-voltage or Normal-voltage Systems\)](#)
- Updated Steps 5, 6 and 8 in [Table 11-7: Serial Instruction Execution for Writing Configuration Registers](#)
- Updated Steps 6 and 8 in [Table 11-8: Serial Instruction Execution for Writing Code Memory](#)
- Updated Steps 6 and 8 in [Table 11-9: Serial Instruction Execution for Writing Data EEPROM](#)
- Updated Entering ICSP™ Mode (see [Figure 11-4](#))
- Updated Steps 4 and 11 in [Table 12-1: Programming the Programming Executive](#)
- Renamed parameters: P12 to P12a and P13 to P13a, and added parameters P12b and P13b in [Table 13-1: AC/DC Characteristics](#)

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NOTES: